

REMARKS

Claims 14, 20, 21 and 23-26 are in the application.

Claims 14, 20, 21 and 23-26 stand rejected under 35 U.S.C. 102(b) as being anticipated by Hshieh (U.S. Patent 6,051,468). These rejections are respectfully traversed, and reconsideration is requested in light of the amendments above and the arguments below.

Independent claim 14, the only independent claim, recites, *inter alia*, a highly conductive layer “comprising a material reacted from a metal and the semiconductor substrate which forms a highly conductive path extending from a first of said plurality of trenches to a second of said plurality of trenches.” Hshieh shows silicide layers 118, but does not show that these layers extend from one trench to another trench. That the silicide layer extends between two trenches is of significance.

The BACKGROUND section of the present application discusses FIG. 1 and the deficiencies of the MOSFET shown in FIG. 1

Nevertheless, the structure 10 of FIG. 1 has two deficiencies. First, the entire active area of the surface of the device is subject to the BPSG etch back. The etching of the BPSG layer 18 can result in large areas on the surface that are subject to damage, defects and contaminants.

Also, the present application states on page 6, lines 12-14:

Another feature is that the process of the invention minimizes the source area over etch problem. Indeed, since the source is protected by the silicide layer 225, there is little or no etching of the source.

The phrase added to the end of paragraph g) of claim 1 was added for the purposes of patentability. The other amendments to the claims were not made for the purposes of patentability

Applicants believe that the present application is in condition for allowance. Applicants respectfully request favorable consideration and that a timely Notice of Allowance be issued in this case.

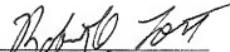
Applicants appreciate the opportunity to call the Examiner, but believe that this amendment to the claims and the forgoing remarks fully address the issues raised by the

Appl. No. 10/618,067
Resp. Dated August 30, 2007.
Reply to Office Action of June 5, 2007.

Examiner. On the other hand, the Examiner is invited to call the undersigned attorney if he has any matters to address that will facilitate allowance of the application.

In the event that Applicants have overlooked the need for an extension of time, additional extension of time, payment of fee, or additional payment of fee, Applicants hereby conditionally petition therefore and authorize that any changes be made to Deposit Account No.: 50-3010.

Respectfully submitted,
HISCOCK & BARCLAY, LLP

By: 

Robert D. Lott
Reg. No. 28,441
2000 HSBC Plaza
100 Chestnut Street
Rochester, NY 14604
Tel: (585) 295-4448
Fax: (585) 295-8465